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(74) Agents: OKABE, Masao et al.; No. 602, Fuji Bldg., 2-3, Marunouchi 3-chome, Chiyoda-ku, Tokyo 1000005 (JP).

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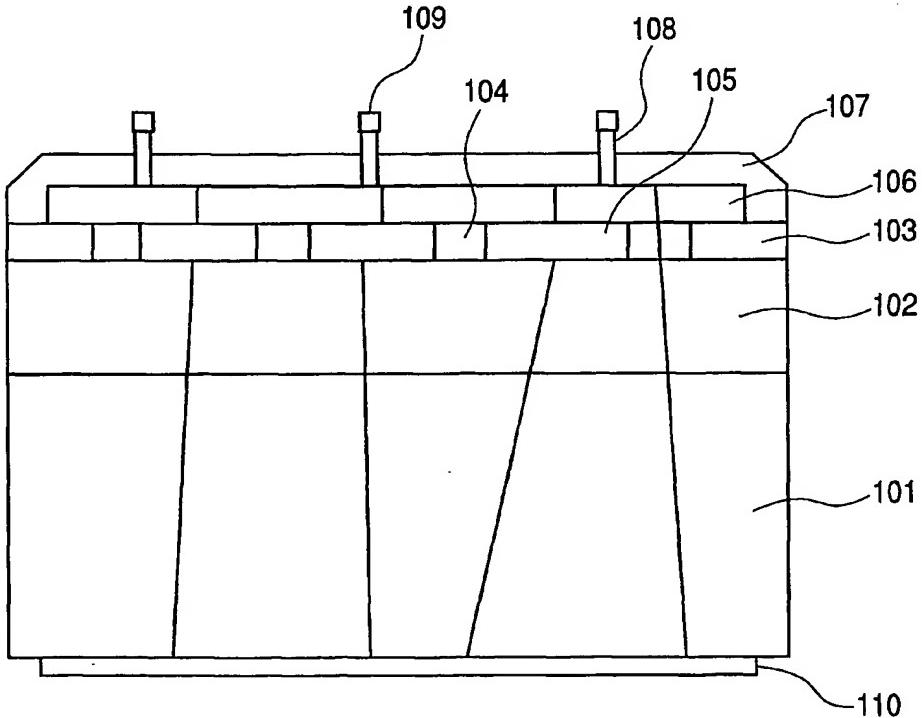
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(54) Title: SOLAR CELL



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(57) Abstract: Provided is a solar cell having a silicon substrate for a solar cell, the substrate being formed by allowing a high-purity polycrystalline silicon layer to grow on a surface of a base that is sliced from a polycrystalline silicon ingot which is obtained by melting metal-grade silicon and solidifying the silicon in one direction, wherein a layer having a non-doped amorphous silicon phase and a microcrystalline silicon phase mixed together is stacked on the high-purity polycrystalline silicon layer.



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